

# MGF0905A

## L, S BAND POWER GaAs FET

### DESCRIPTION

The MGF0905A, GaAs FET with an N-channel schottky gate, is designed for use in UHF band amplifiers.

### FEATURES

- High output power  
 $P_o = 34\text{dBm (TYP.) @ } f = 1.65\text{GHz, } P_{in} = 26\text{dBm}$
- High power gain  
 $G_p = 8\text{dB (TYP.) @ } f = 1.65\text{GHz, } P_{in} = 26\text{dBm}$
- High power added efficiency  
 $\eta_{add} = 40\% \text{ (TYP.) @ } f = 1.65\text{GHz, } P_{in} = 26\text{dBm}$

### APPLICATION

For UHF Band power amplifiers

### QUALITY GRADE

- GG

### RECOMMENDED BIAS CONDITIONS

- $V_{DS} = 8\text{V}$
- $I_D = 800\text{mA}$
- $R_g = 100\Omega$
- Refer to Bias Procedure

### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Ratings	Unit
$V_{GS0}$	Gate to source voltage	-17	V
$V_{GDO}$	Gate to drain voltage	-17	V
$I_D$	Drain current	3200	mA
$I_{GR}$	Reverse gate current	-10	mA
$I_{GF}$	Forward gate current	21.5	mA
$P_T$	Total power dissipation *1	12	W
$T_{ch}$	Channel temperature	175	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-65 ~ +175	$^\circ\text{C}$

\*1:  $T_C = 25^\circ\text{C}$

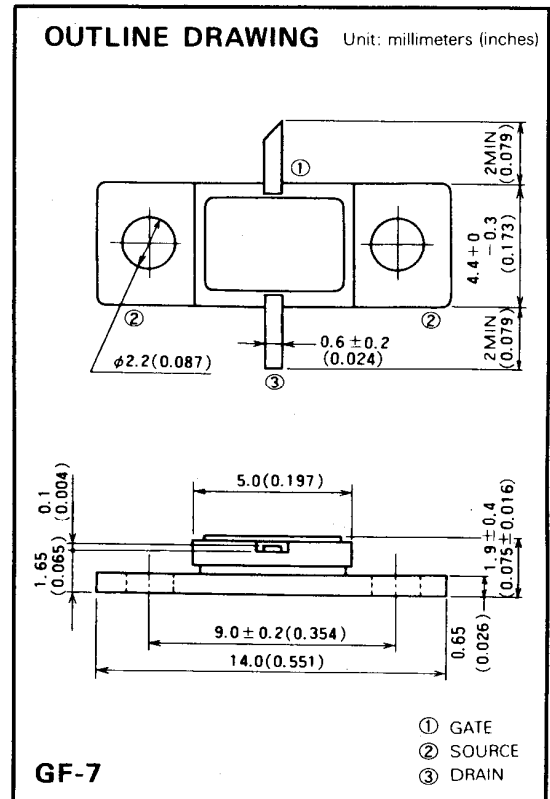
### ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$I_{DSS}$	Saturated drain current	$V_{DS} = 3\text{V, } V_{GS} = 0\text{V}$	1600	2400	3200	mA
$V_{GS(off)}$	Gate to source cut-off voltage	$V_{DS} = 3\text{V, } I_D = 10\text{mA}$	-1	-3	-5	V
$g_m$	Transconductance	$V_{DS} = 3\text{V, } I_D = 800\text{mA}$	500	800	—	mS
$P_o$	Output power	$V_{DS} = 8\text{V, } I_D = 800\text{mA, } f = 1.65\text{GHz, } P_{in} = 26\text{dBm}$	33	34	—	dBm
$\eta_{add}$	Power added efficiency		—	40	—	%
$R_{th(ch-c)}$	Thermal resistance *1	$\Delta V_f$ method	—	—	12.5	$^\circ\text{C/W}$
$R_{th(ch-a)}$	Thermal resistance *2	$\Delta V_f$ method	—	—	72.5	$^\circ\text{C/W}$

\*1: Channel to case    \*2: Channel to ambient

### OUTLINE DRAWING

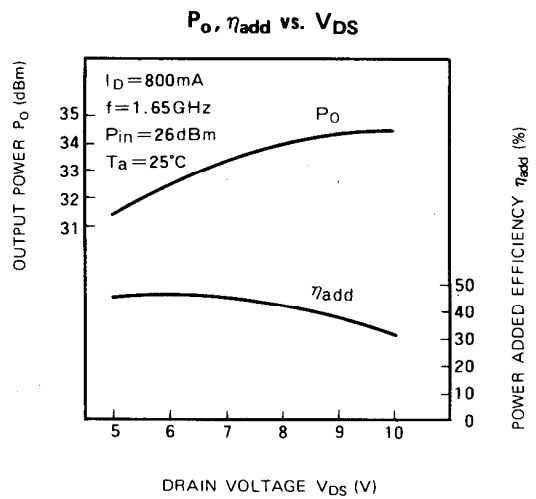
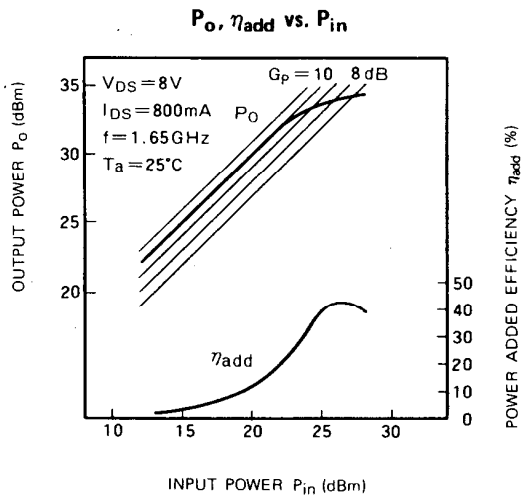
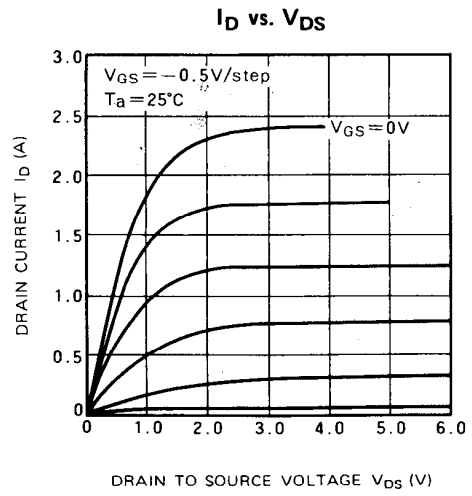
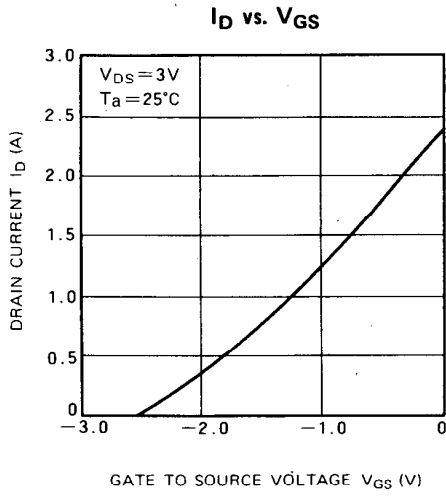
Unit: millimeters (inches)



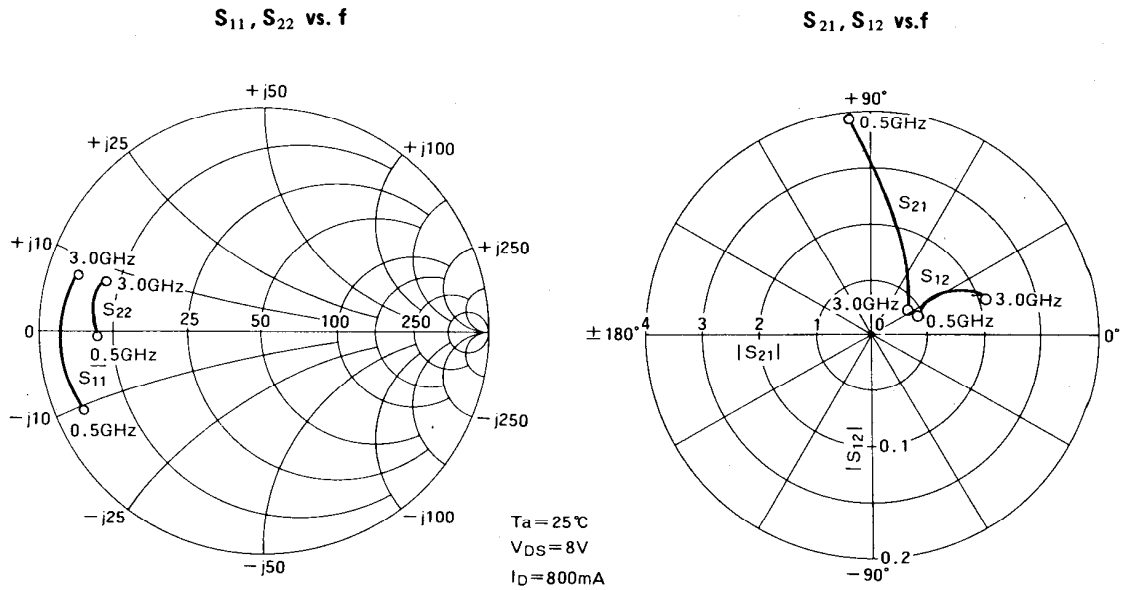
GF-7

**L, S BAND POWER GaAs FET**

**TYPICAL CHARACTERISTICS**



**L, S BAND POWER GaAs FET**



**S PARAMETERS** ( $T_a = 25^\circ\text{C}$ ,  $V_{DS} = 8\text{V}$ ,  $I_D = 800\text{mA}$ )

f (GHz)	$S_{11}$		$S_{21}$		$S_{12}$		$S_{22}$		K	MSG/MAG dB
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)		
0.5	0.861	-155.5	3.895	96.0	0.022	25.0	0.731	-179.0	0.806	22.5
1.0	0.887	-170.5	1.999	78.0	0.025	33.0	0.753	175.5	1.133	16.8
1.5	0.894	177.0	1.485	68.0	0.033	33.0	0.747	172.5	1.175	14.0
2.0	0.887	173.0	1.205	58.0	0.039	29.0	0.743	169.5	1.205	12.2
2.5	0.877	169.0	1.000	48.5	0.047	24.0	0.738	166.5	1.221	10.4
3.0	0.864	165.0	0.795	35.0	0.054	18.0	0.723	164.0	1.365	8.1

**Requests Regarding Safety Designs**

Mitsubishi Electric constantly strives to raise the level of its quality and reliability. Despite these concerted efforts, however, there will be occasions when our semiconductor products suffer breakdowns, malfunctions or other problems. In view of this reality, it is requested that every feasible precaution be taken in the pursuit of redundancy design, malfunction prevention design and other safety-related designs, to prevent breakdowns or malfunctions in our products from resulting in accidents involving people, fires, social losses or other problems, thereby upholding the highest levels of safety in the products when in use by customers.

**Matters of Importance when Using these Materials**

1. These materials are designed as reference materials to ensure that all customers purchase Mitsubishi Electric semiconductors best suited to their specific use applications. Please be aware, however, that the technical information contained in these materials does not comprise consent for the execution or use of intellectual property rights or other rights owned by Mitsubishi Electric Corporation.
2. Mitsubishi Electric does not assume responsibility for damages resulting from the use of product data, graphs, charts, programs, algorithms or other applied circuit examples described in these materials, or for the infringement of the rights of third-party owners resulting from such use.
3. The data, graphs, charts, programs, algorithms and all other information described in these materials were current at the issue of these materials, with Mitsubishi Electric reserving the right to make any necessary updates or changes in the products or specifications in these materials without prior notice. Before purchasing Mitsubishi Electric semiconductor products, therefore, please obtain the latest available information from Mitsubishi Electric directly or an authorized dealer.
4. Every possible effort has been made to ensure that the information described in these materials is fully accurate. However, Mitsubishi Electric assumes no responsibility for damages resulting from inaccuracies occurring within these materials.
5. When using the product data, technical contents indicated on the graphs, charts, programs or algorithms described in these materials, assessments should not be limited to only the technical contents, programs and algorithm units. Rather, it is requested that ample evaluations be made of each individual system as a whole, with the customer assuming full responsibility for decisions on the propriety of application. Mitsubishi Electric does not accept responsibility for the propriety of application.
6. The products described in these materials, with the exception of special mention concerning use and reliability, have been designed and manufactured with the purpose of use in general electronic machinery. Accordingly these products have not been designed and manufactured with the purpose of application in machinery or systems that will be used under conditions that can affect human life, or in machinery or systems used in social infrastructure that demand a particularly high degree of reliability. When considering the use of the products described in these materials in transportation machinery (automobiles, trains, vessels), for objectives related to medical treatment, aerospace, nuclear power control, submarine repeaters or systems or other specialized applications, please consult with Mitsubishi Electric directly or an authorized dealer.
7. When considering use of products for purposes other than the specific applications described in these materials, please inquire at Mitsubishi Electric or an authorized dealer.
8. The prior consent of Mitsubishi Electric in writing is required for any reprinting or reproduction of these materials.
9. Please direct any inquiries regarding further details of these materials, or any other comments or matters of attention, to Mitsubishi Electric or an authorized dealer.